

## Supplementary Information

### Room-temperature electrochemical deposited polycrystalline SnO<sub>2</sub> with adjustable work function for high-efficiency perovskite solar cells

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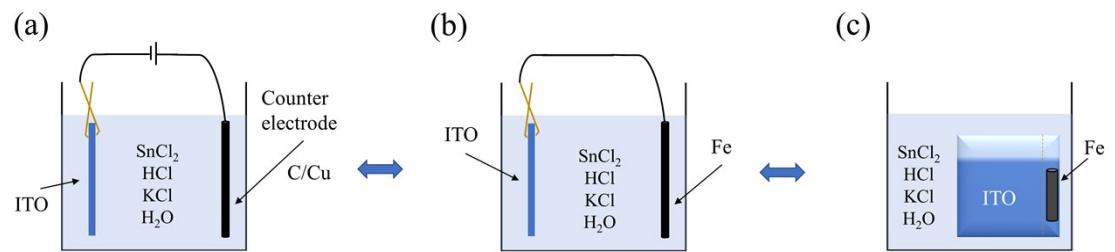
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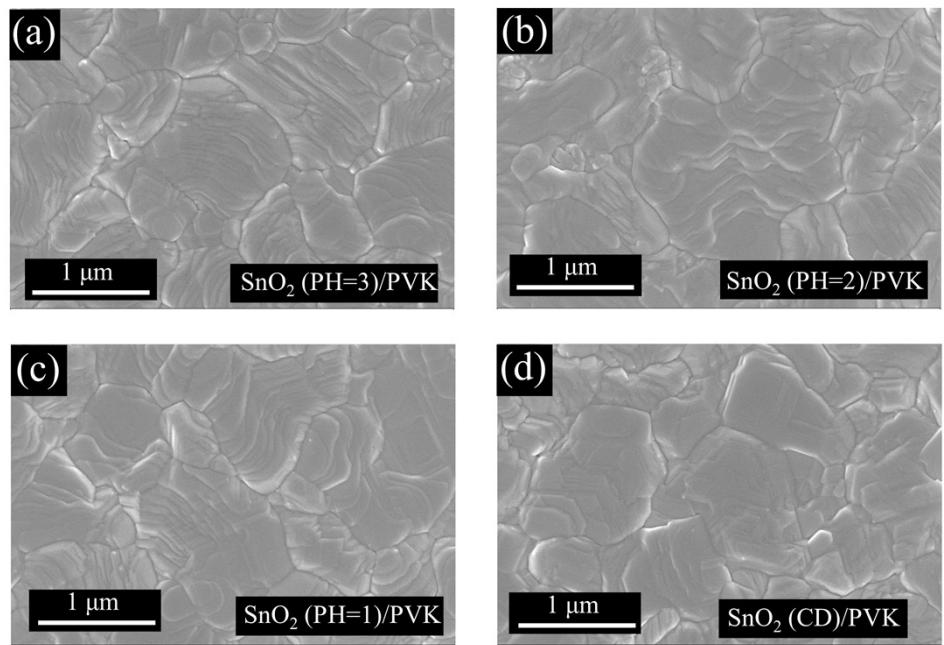
#### This PDF file includes:

Figs. S1 to S11

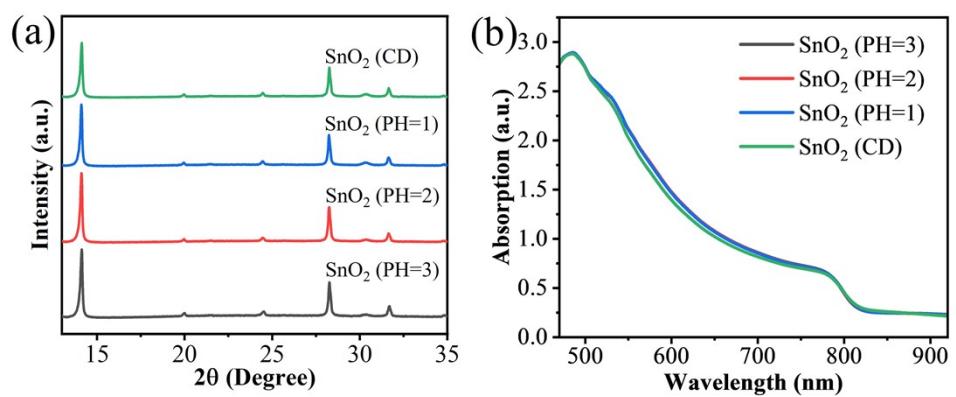
Tables S1 to S7



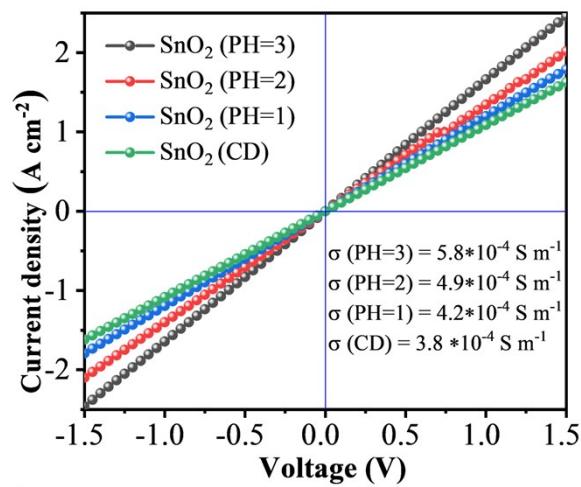
**Fig. S1.** (a-c) Equivalence principle schematic diagram of the deposition process.



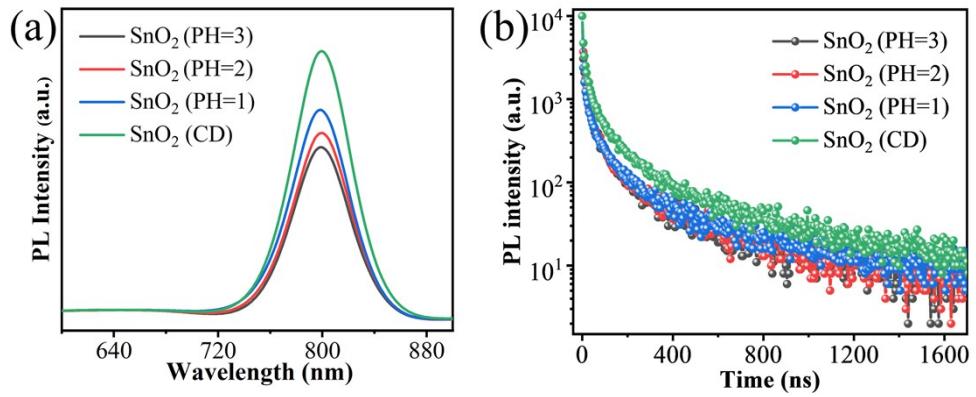
**Fig. S2.** (a-d) The SEM images of perovskite films on different SnO<sub>2</sub> films.



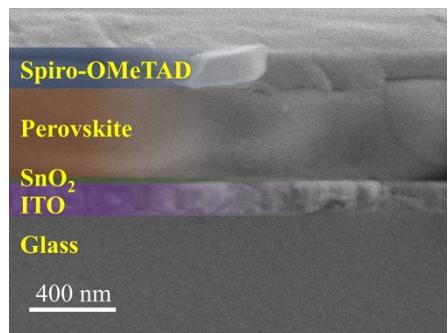
**Fig. S3.** (a) The XRD patterns and (b) the absorption spectrums of perovskite films on different  $\text{SnO}_2$  films.



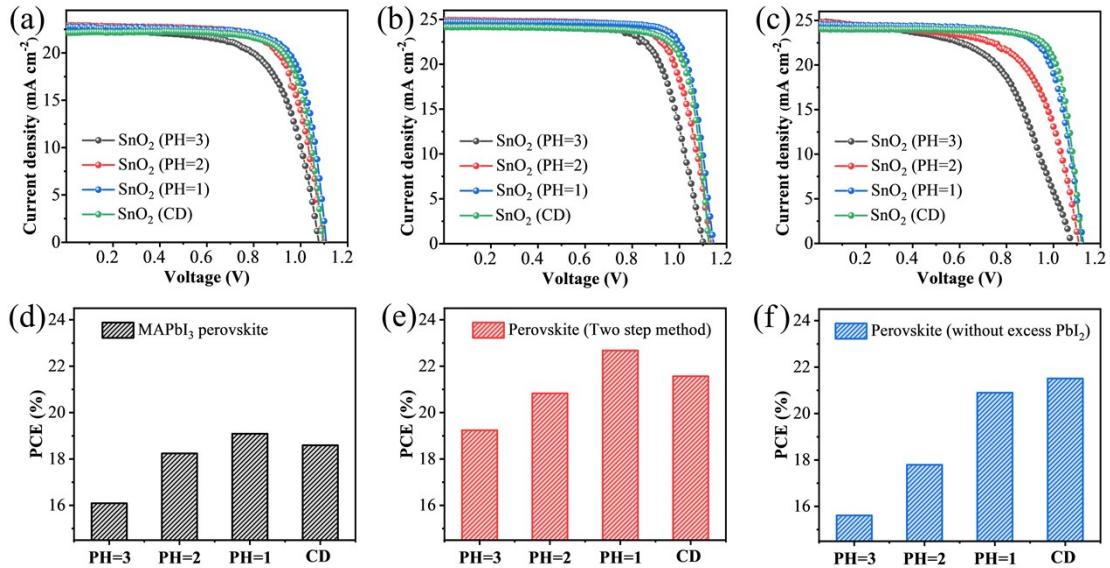
**Fig. S4.** The conductivity test of  $\text{SnO}_2$  films using the  $J$ - $V$  curves.



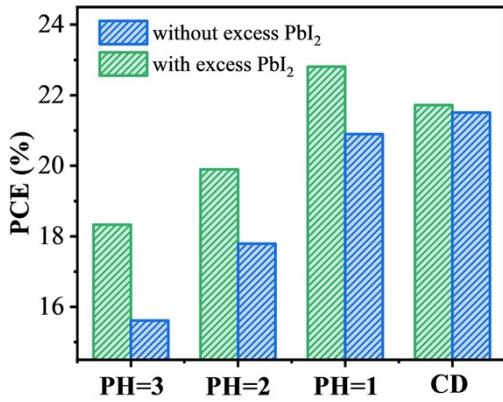
**Fig. S5.** (a) The PL curves and (b) the TRPL curves of perovskite films on different  $\text{SnO}_2$  films.



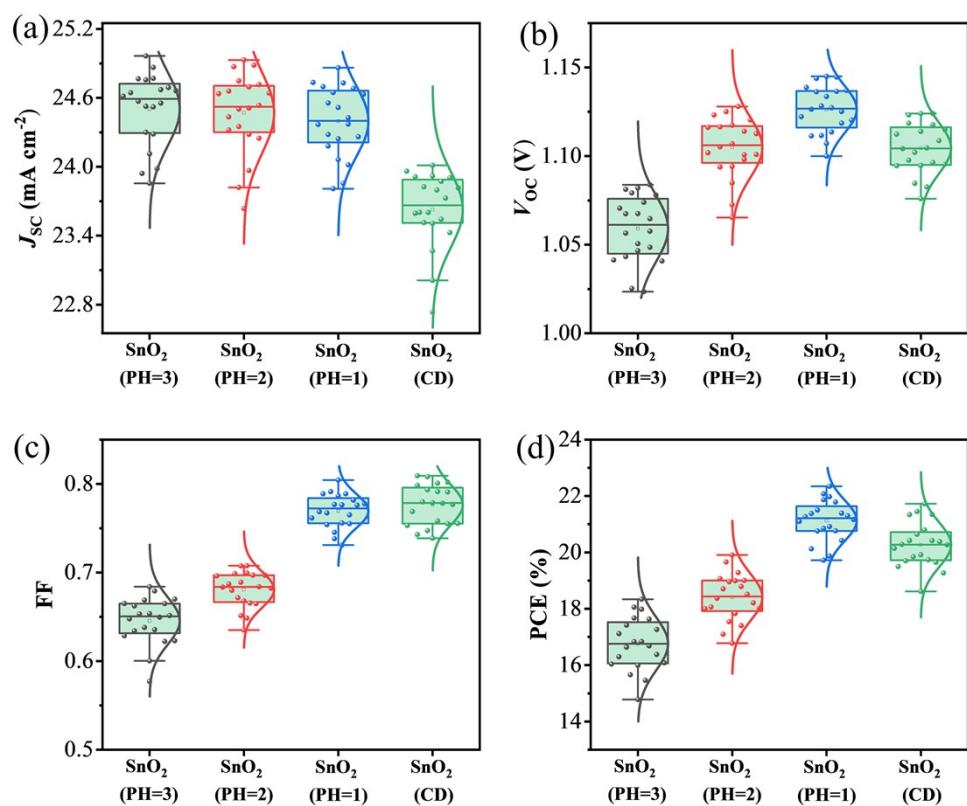
**Fig. S6.** The cross-sectional SEM image of device.



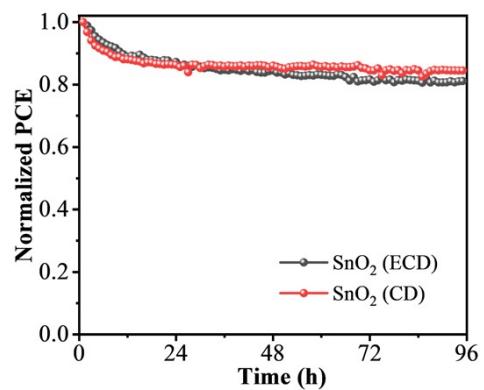
**Fig. S7.** (a) The reverse scanning  $J$ - $V$  curves and (d) the PCE for MAPbI<sub>3</sub> devices based on different SnO<sub>2</sub> films. (b) The reverse scanning  $J$ - $V$  curves and (e) the PCE for two-step method (FAPbI<sub>3</sub>)<sub>0.93</sub>(MAPbI<sub>3</sub>)<sub>0.07</sub> perovskite devices based on different SnO<sub>2</sub> films. (c) The reverse scanning  $J$ - $V$  curves and (f) the PCE for FAPbI<sub>3</sub> perovskite without excess PbI<sub>2</sub> devices based on different SnO<sub>2</sub> films.



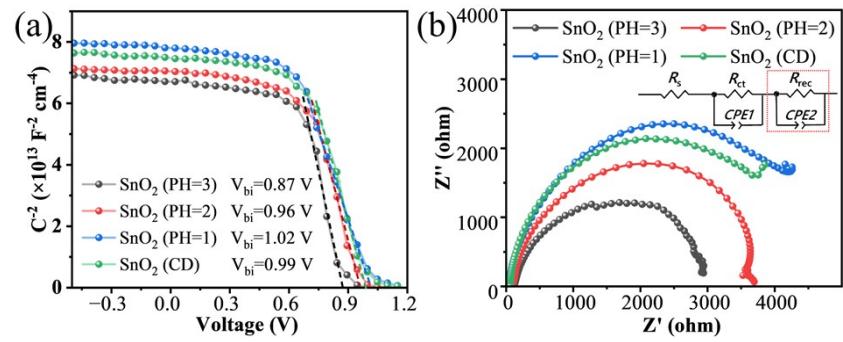
**Fig. S8.** The comparison figure of the device performance before and after adding excessive PbI<sub>2</sub> for different SnO<sub>2</sub> films.



**Fig. S9.** (a-d) The photovoltaic parameters statistics chart for devices based on different  $\text{SnO}_2$  films.



**Fig. S10.** Maximum power point tracking for device with different SnO<sub>2</sub> preparation methods measured under 1 Sun illumination without ultraviolet filter.



**Fig. S11.** (a) Mott–Schottky fitting to the  $C^{-2}$ - $V$  curves of different devices. (b) Nyquist plots of different devices measured in the dark.

**Table S1.** Comparison the performance of the state-of-the-art PSCs of the low temperature prepared SnO<sub>2</sub> reported in the literature (PCEs denote champion values).

Preparation method	PCE (%)	J <sub>SC</sub> (mA cm <sup>-2</sup> )	V <sub>OC</sub> (mV)	FF (%)	Temperat -ure (°C)	Year	Ref.
<b>Electrochemical Deposited</b>	22.85	24.83	1144	80.44	25	-	This work
<b>Commercially Colloidal Dispersion</b>	21.72	23.92	1124	80.09	150	-	This work
<b>Cd-SnO<sub>2</sub> nanocrystals</b>	21.73	23.81	1090	84.00	90	2022	<sup>1</sup>
<b>Mesoporous SnO<sub>2</sub> and RbF modification</b>	22.72	24.50	1148	82.10	180	2021	<sup>2</sup>
<b>Vacuum-assisted annealed SnO<sub>2</sub> Colloidal Dispersion</b>	20.14	22.76	1140	77.62	100	2022	<sup>3</sup>
<b>MXene-SnO<sub>2</sub> Colloidal Dispersion</b>	19.14	24.16	1070	74.05	150	2020	<sup>4</sup>
<b>Non-Aqueous One-Pot SnO<sub>2</sub> Nanoparticle Inks</b>	18.40	21.88	1120	75.00	140	2022	<sup>5</sup>
<b>Heterophase SnO<sub>2</sub> Electron Transport Bilayer</b>	20.39	23.26	1125	77.92	190	2020	<sup>6</sup>
<b>HEPES-Au NSs-modified SnO<sub>2</sub> Colloidal Dispersion</b>	21.13	23.12	1150	79.04	150	2022	<sup>7</sup>
<b>Zr/F Co-Doped SnO<sub>2</sub></b>	19.19	24.39	1105	71.20	200	2020	<sup>8</sup>
<b>Compact SnO<sub>2</sub> layer @ SnO<sub>2</sub> nanosheets</b>	16.17	22.76	1050	68.00	95	2016	<sup>9</sup>
<b>Energetically favored formation of SnO<sub>2</sub></b>	19.20	22.20	1170	74.00	80	2017	<sup>10</sup>
<b>Atomically Coherent Interlayers on</b>	25.50	25.74	1189	83.20	190	2021	<sup>11</sup>
<b>Chemical Bath Deposition</b>	25.20	25.14	1181	84.80	170	2021	<sup>12</sup>
<b>Conformal Quantum dot-SnO<sub>2</sub></b>	25.39	26.28	1177	81.49	100	2022	<sup>13</sup>

**Table S2.** The average surface potentials of different SnO<sub>2</sub> films.

	<b>SnO<sub>2</sub>(PH=3)</b>	<b>SnO<sub>2</sub>(PH=2)</b>	<b>SnO<sub>2</sub>(PH=1)</b>	<b>SnO<sub>2</sub>(CD)</b>
<b>KPFM (eV)</b>	4.32	4.46	4.55	4.68

**Table S3.** Energy band parameters of different SnO<sub>2</sub> films.

	<b>SnO<sub>2</sub>(PH=3)</b>	<b>SnO<sub>2</sub>(PH=2)</b>	<b>SnO<sub>2</sub>(PH=1)</b>	<b>SnO<sub>2</sub>(CD)</b>
<b><math>E_{\text{cutoff}}</math> (eV)</b>	16.99	16.86	16.72	16.59
<b><math>W_F</math> (eV)</b>	4.23	4.36	4.50	4.63
<b><math>E_{\text{onset}}</math> (eV)</b>	3.53	3.50	3.46	3.40
<b><math>E_{\text{VB}}</math> (eV)</b>	-7.76	-7.86	-7.96	-8.03
<b><math>E_{\text{CB}}</math> (eV)</b>	-4.13	-4.20	-4.29	-4.35

**Table S4.** Results of the double exponential fitting of TRPL spectra.

Sample	A <sub>1</sub> (%)	τ <sub>1</sub> (ns)	A <sub>2</sub> (%)	τ <sub>2</sub> (ns)	τ (ns)
<b>SnO<sub>2</sub> (PH=3)</b>	91.23	25.87	8.77	196.78	98.06
<b>SnO<sub>2</sub> (PH=2)</b>	93.06	27.64	6.93	231.23	105.79
<b>SnO<sub>2</sub> (PH=1)</b>	89.75	26.57	10.25	212.45	115.29
<b>SnO<sub>2</sub> (CD)</b>	88.83	37.17	11.17	251.57	135.73

**Table S5.** Photovoltaic performances of  $\text{MAPbI}_3$  devices based on different  $\text{SnO}_2$  films.

Material	$J_{\text{SC}}$ ( $\text{mA cm}^{-2}$ )	$V_{\text{OC}}$ (mV)	FF (%)	PCE (%)
$\text{SnO}_2$ (PH=3)	22.79	1077	65.55	16.09
$\text{SnO}_2$ (PH=2)	22.93	1100	72.31	18.24
$\text{SnO}_2$ (PH=1)	22.75	1109	75.66	19.09
$\text{SnO}_2$ (CD)	22.16	1094	76.68	18.59

**Table S6.** Photovoltaic performances of two step method  $(\text{FAPbI}_3)_{0.93}(\text{MAPbI}_3)_{0.07}$  perovskite devices based on different  $\text{SnO}_2$  films.

Material	$J_{\text{SC}} (\text{mA cm}^{-2})$	$V_{\text{OC}} (\text{mV})$	FF (%)	PCE (%)
$\text{SnO}_2 (\text{PH}=3)$	24.66	1101	70.86	19.24
$\text{SnO}_2 (\text{PH}=2)$	24.91	1134	73.74	20.83
$\text{SnO}_2 (\text{PH}=1)$	24.73	1145	80.10	22.68
$\text{SnO}_2 (\text{CD})$	24.17	1124	79.40	21.57

**Table S7.** Photovoltaic performances of FAPbI<sub>3</sub> perovskite without excess PbI<sub>2</sub> devices based on different SnO<sub>2</sub> films.

Material	<i>J</i> <sub>SC</sub> (mA cm <sup>-2</sup> )	<i>V</i> <sub>OC</sub> (mV)	FF (%)	PCE (%)
SnO <sub>2</sub> (PH=3)	24.84	1074	58.51	15.61
SnO <sub>2</sub> (PH=2)	24.78	1108	64.79	17.79
SnO <sub>2</sub> (PH=1)	24.53	1128	75.53	20.90
SnO <sub>2</sub> (CD)	24.02	1119	80.03	21.51

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